WHAT IS CLAIMED IS:

1.   A method of archiving data in a memory, comprising the steps of:

(a)   classifying the data according to a desired lifetime thereof; and

(b)   archiving the data in the memory using a storage method having a reliability in accordance with said desired lifetime.

2.   The method of claim 1, wherein said storage method includes a parameter, a value whereof is set in accordance with said classifying to control said reliability.

3.   The method of claim 2, wherein said parameter is a programming voltage pulse increment.

4.   The method of claim 2, wherein said parameter is a target threshold voltage.

5.   The method of claim 2, wherein said parameter is a programming voltage pulse width.

6.   The method of claim 2, wherein said parameter is a starting programming voltage.

7.   The method of claim 2, wherein said parameter is a maximum number of programming voltage pulses.

8. The method of claim 2, wherein said parameter is a maximum programming voltage.

9. The method of claim 2, wherein said parameter is a number of levels per cell of the memory.

10. A system for archiving data, comprising:

(a) a mechanism for classifying the data according to a desired lifetime thereof; and

(b) a memory having a controller operative to archive the data in said memory using a storage method having a reliability in accordance with said desired lifetime.

11. The system of claim 10, wherein said mechanism includes a processor for running an application that produces and classifies the data.

12. The system of claim 10, wherein said mechanism includes an input device wherewith a user classifies the data.

13. The system of claim 10, wherein said memory is a non-volatile memory.

14. The system of claim 10, wherein said storage method includes a parameter, a value whereof is set in accordance with said classifying to control said reliability.

15.   The system of claim 14, wherein said memory is an EPROM including a plurality of cells.

16.   The system of claim 15, wherein said parameter is an increment of a voltage pulse used to program said cells.

17.   The system of claim 15, wherein said parameter is a target threshold voltage of said cells.

18.   The system of claim 15, wherein said parameter is a width of programming voltage pulses used to program said cells.

19.   The system of claim 15, wherein said parameter is a starting voltage used to program said cells.

20.   The system of claim 15, wherein said parameter is a maximum number of programming voltage pulses used to program said cells.

21.   The system of claim 15, wherein said parameter is a maximum voltage used to program said cells.

22.   The system of claim 15, wherein said parameter is a number of programming levels of said cells.